

# LC895840



## CD-R Strategy IC

Preliminary

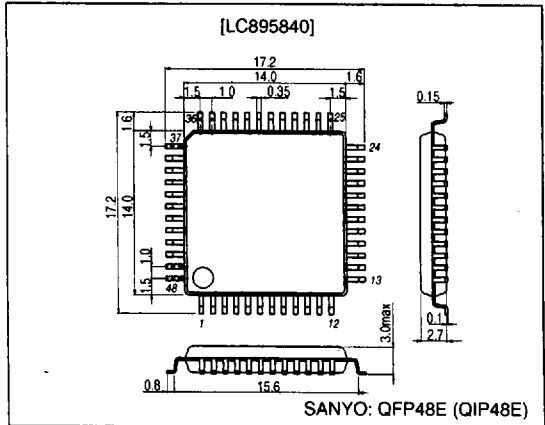
### Functions and Applications

Performs signal amplitude and delay time adjustment for output EFM signal of the LC895926 to generate and output suitable signal for recording.  
Generates a sampling pulse synchronized with EFM output.

### Package Dimensions

unit: mm

3156-QFP48E



### Specifications

Absolute Maximum Ratings at  $V_{SS} = 0$  V

Parameter	Symbol	Conditions	Ratings	Unit
Maximum supply voltage	$V_{DD}$ max	$T_a = 25^\circ\text{C}$	-0.3 to +7.0	V
Input/output voltage	$V_I, V_O$	$T_a = 25^\circ\text{C}$	-0.3 to $V_{DD} + 0.3$	V
Operating temperature	$T_{opg}$		-30 to +70	$^\circ\text{C}$
Storage temperature	$T_{str}$		-55 to +125	$^\circ\text{C}$
Allowable power dissipation	$P_d$		350	mW

Allowable Operating Ranges at  $T_a = -30$  to  $+70^\circ\text{C}$ ,  $V_{SS} = 0$  V

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Supply voltage (5 V system)	$V_{DD}$		4.5	5.0	5.5	V
Supply voltage (3.3 V system)	$V_{DD}$		3.0	3.3	3.6	V
Input voltage range	$V_{IN}$		0		$V_{DD}$	V

DC Characteristics at  $T_a = -30$  to  $+70^\circ\text{C}$ ,  $V_{SS} = 0$  V,  $V_{DD} = 4.5$  to  $5.5$  V

Parameter	Symbol	Conditions	Ratings			Unit	Applicable pins *
			min	typ	max		
High-level input voltage	$V_{IH}$		2.2		—	V	(2), (4)
Low-level input voltage	$V_{IL}$		—		0.8	V	(2), (4)
High-level input voltage	$V_{IH}$		$0.7 V_{DD}$		—	V	(1)
Low-level input voltage	$V_{IL}$		—		$0.3 V_{DD}$	V	(1)
High-level output voltage	$V_{OH}$	$I_{OH} = -8$ mA			$V_{DD} - 2.1$	V	(3), (4)
Low-level output voltage	$V_{OL}$	$I_{OL} = 8$ mA			0.4	V	(3), (4)

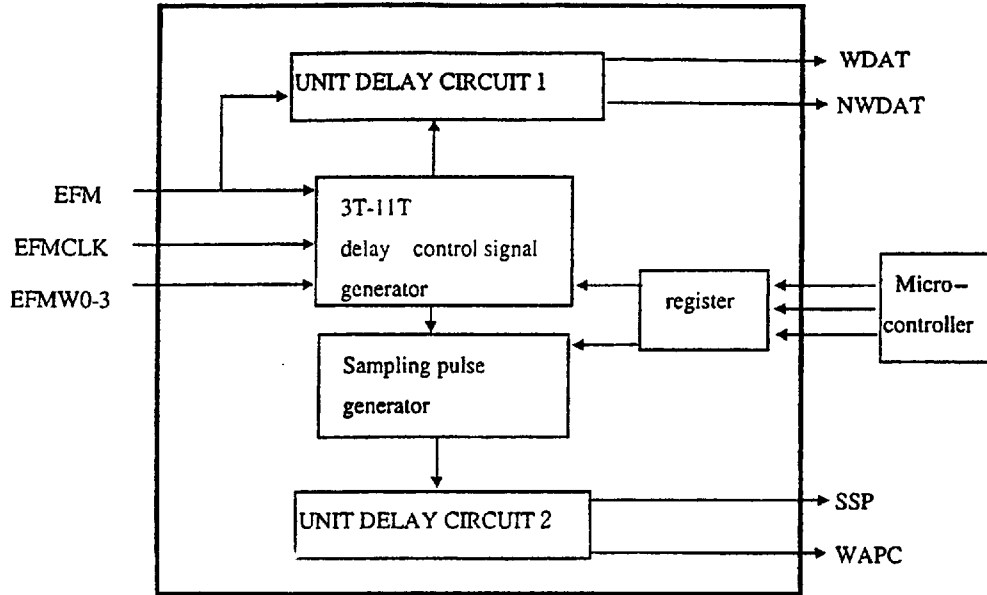
Note: \* The applicable pin sets are as follows. However, analog-related pins are excluded.

- (1) (INPUT CMOS LEVEL) EFMCK
- (2) (INPUT TTL LEVEL) RESETB, SUA0 to SUA4, SMS, CSB, RDB, WRB, WRITE, EFM, EFMW3 to 0
- (3) (OUTPUT) TEST0, TEST1, WDAT, NWDAT, SSP, WAPC, H11TO, LDH
- (4) (BI-DIRECTION) D0 to D7

**SANYO Electric Co., Ltd. Semiconductor Company**

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taite-ku, TOKYO, 110-8534 JAPAN

Block Diagram



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